

PATENT APPLICATION

Sheet 1 of 6

FORM PTO-1449 LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	ATTY. DOCKET NO. 200316547-1	APPLICATION NO. 10/799961	CONFIRMATION NO.
	APPLICANT Randy L. Hoffman, et al.		
	FILING DATE March 12 3/12/04	GROUP 2815	

REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
WFK	1A	5,744,864	08/28/1998	Cillessen, et al.	
WFK	1B	2003/0047785	03/13/2003	Kawasaki, et al.	
WFK	1C	2003/0111663	06/19/2003	Yagi	
WFK	1D	2003/0218221	11/27/2003	Wager, III, et al.	
WFK	1E	2003/0218222	11/27/2003	Wager, III, et al.	
WFK	1F	60/490,239	07/25/2003		Transparent Thin Film Transistor with Zinc-Tin Oxide Channel...
WFK	1G	10/763,353	01/23/2004		Semiconductor Device
WFK	1H	10/763,354	01/23/2004		Transistor Including a Deposited Channel Region Having A ...
	1I				
	1J				
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FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	Pages/Columns/Lines Where Relevant Passages/Figures Appear	Check if Translation attached
WFK	1L	WO 97/06544	02/20/1997	Cillessen, et al.		E
WFK	1M	EP1134811	09/19/2001	Kawasaki, et al.		
	1N					
	1O					
	1P					

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

WFK	1Q	Aoki, Akira, et al., "Tin Oxide Thin Film Transistors", Japan J. Appl. Phys., Vol. 9, p.582 (1970).
WFK	1R	Carcia, P.F., et al., "Transparent ZnO thin-film transistor fabricated by rf magnetron sputtering", Applied Physics Letters, Vol. 82, No. 7, pp. 1117-1119 (February 17, 2003).
WFK	1S	Carcia, P.F., et al., "ZnO Thin Film Transistors for Flexible Electronics", Mat. Res. Soc. Symp. Proc., Vol. 769, pp. H72.1-H72.6 (2003).

EXAMINER <i>William F. Kraig</i>	DATE CONSIDERED 1/6/06
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	2L				
	2M				
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	2O				
	2P				

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

WFK	2Q	Fu, Shelton, et al., "MOS and MOSFET with Transistion Metal Oxides", SPIE Vol. 2697, pp. 520-527.
WFK	2R	Giesbers, J.B., et al., "Dry Etching of All-Oxide Transparent Thin Film Memory Transistors", Microeletronic Engineering, Vol. 35, pp. 71-74 (1997).
WFK	2S	Grosse-Holz, K.O., et al., "Semiconductive Behavior of Sb Doped SnO2 Thin Films", Mat. Res. Soc. Symp. Proc., Vol. 401, pp. 67-72 (1996).

EXAMINER

William F. Kraig

DATE CONSIDERED

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	3L				
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	3P				

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

WFK	3Q	Hoffman, R.L., et al., "ZnO-based transparent thin-film transistors", Applied Physics Letters, Vol. 82, No. 5, pp. 733-735 (February 3, 2003).
WFK	3R	Masuda, Satoshi, et al., "Transparent thin film transistors using ZnO as an active channel layer and their electrical properties", Journal of Applied Physics, Vol. 93, No. 3, pp. 1624-1630 (February 1, 2003).
WFK	3S	Nishi, Junya, et al., "High Mobility Thin Film Transistors with Transparent ZnO Channels", Jpn. J. Appl. Phys., Vol. 42, Part 2, No. 4A, pp. L347-L349 (April, 2003).

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William F. Kraig

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PATENT APPLICATION

Sheet 4 of 6

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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

WFK	4Q	Ohya, Yutaka, et al., "Thin Film Transistor of ZnO Fabricated by Chemical Solution Deposition", Jpn. J. Appl. Phys., Vol. 40, Part 1, No. 1, pp. 297-298 (January, 2001).
WFK	4R	Pallecchi, Ilaria, et al. "SrTiO3-based metal-insulator-semiconductor heterostructures" Applied Physics Letters, Vol. 78, No. 15, pp. 2244-2246 (April 9, 2001).
WFK	4S	Prins, M. W. J., et al., "A ferroelectric transparent thin-film transistor", Appl. Phys. Lett., Vol. 68, No. 25, pp. 3650-3652 (June 17, 1996).

EXAMINER	DATE CONSIDERED
<i>William F. King</i>	1/6/06

FORM PTO-1449 LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	ATTY. DOCKET NO.	APPLICATION NO.	CONFIRMATION NO.
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	5L				
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	5P				

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

WFK	5Q	Seager, C.H., et al., "Charge Trapping and device behavior in ferroelectric memories", Appl. Phys. Lett., Vol. 68, No. 19, pp. 2660-2662 (May 6, 1996).
WFK	5R	Uneno, K., et al. "Field-effect transistor on SrTiO ₃ with sputtered Al ₂ O ₃ gate insulator", Applied Physics Letters, Vol. 83, No. 9, pp. 1755-1757 (September 1, 2003).
WFK	5S	Wöllenstein, Jürgen, et al., "An insulated gate thin-film transistor using SnO ₂ as semiconducting channel, a possible new gas sensor device" The 11th European Conference on Solid State Transducers, pp. 471-474 (September 21-24, 1997).

EXAMINER

William F. Krey

DATE CONSIDERED

11/6/06

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	200316547-1	10179961	
	APPLICANT		
	Randy L. Hoffman, et al.		
	FILING DATE	GROUP	
	March 3/12/04	2815	

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	6O				
	6P				

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

WFK	6Q	Yoshida, A., "Three Terminal Field Effect Superconducting Device Using SrTiO ₃ Channel" IEEE Transactions on Applied Superconductivity, Vol. 5, No. 2, pp. 2892-2895 (June, 1995).
WFK	6R	Solid-State Electronics, Vol. 7, Pergamon Press, Notes pp. 701-702 (1964).
WFK	6S	Anonymous, "Transparent and/or memory thin film transistors in LCD's and PLEAD_" Research Disclosure, p. 890 (July 1998).

EXAMINER

William F. King

DATE CONSIDERED

1/6/06

PTO/SB/08A (08-03)

Approved for use through 07/31/2006. OMB 0651-0031

U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

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Substitute for form 1449/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Sheet	1	of	2
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Complete if Known

Application Number	10/799961
Filing Date	Mar 12, 2004
First Named Inventor	Randy Hoffman
Art Unit	2815
Examiner Name	William F. Kraig
Attorney Docket Number	2003316547-1

U. S. PATENT DOCUMENTS

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FOREIGN PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Cite No.	Foreign Patent Document	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear
		Country Code* ¹ Number* ² Kind Code* ³ (if known)	MM-DD-YYYY		
WFK		WO 02/09157	01-31-2002	Motorola	✓

Examiner Signature	<i>William J. Kreis</i>	Date Considered	1/6/06
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Substitute for form 1449/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)		Complete if Known	
		Application Number	10/799961
		Filing Date	Mar 12, 2004
		First Named Inventor	Randy Hoffman
		Art Unit	2815
Examiner Name	William F. Kraig		
Sheet 2	of 2	Attorney Docket Number	200316547-1

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
WFK		MINAMI, T., "New transparent conducting ZnO-In2O3 thin films...", Thin Solid Films, vol. 317, no. 1-2, Apr 1, 1998, pgs. 318-321.	
WFK		MINAMI, T., "Preparation of transparent conducting In4Sn3O12...", Thin Solid Films, vol.308-309, Oct 31, 1997, pgs. 13-18.	

Examiner Signature	<i>William F. Kraig</i>	Date Considered	1/6/06
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¹ Applicant's unique citation designation number (optional). ² Applicant is to place a check mark here if English language Translation is attached. This collection of information is required by 37 CFR 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

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